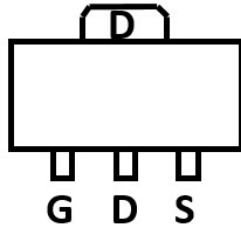
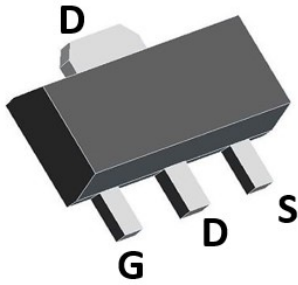
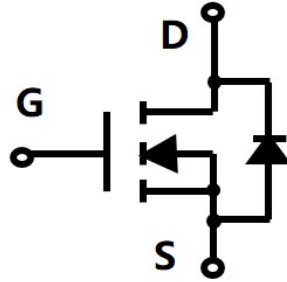


N-Channel Enhancement Mode Field Effect Transistor



SOT-89



Product Summary

- V_{DS} 60V
- I_D 3.5A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $<100m\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) $<120m\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=2.5V$) $<200m\Omega$

General Description

- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 16	V
Drain Current	$T_A=25^\circ\text{C}$	I_D	3.5	A
	$T_A=70^\circ\text{C}$		2.8	
Pulsed Drain Current ^A		I_{DM}	14	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$ Steady State		P_D	1.7	W
Thermal Resistance Junction-to-Ambient ^B		$R_{\theta JA}$	74	$^\circ\text{C/W}$
Junction and Storage Temperature Range		T_J, T_{STG}	$-55\sim+150$	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJH03N06B	F1	6003	1000	10000	40000	7" reel



YJH03N06B

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V,V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =± 16V, V _{DS} =0V			± 100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.65	0.95	1.55	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 3A		86	100	mΩ
		V _{GS} = 4.5V, I _D = 2A		90	120	
		V _{GS} = 2.5V, I _D = 1A		100	200	
Diode Forward Voltage	V _{SD}	I _S = 3.0A,V _{GS} =0V		0.8	1.2	V
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =30V,V _{GS} =0V,f=1MHZ		451		pF
Output Capacitance	C _{oss}			38		
Reverse Transfer Capacitance	C _{rss}			31		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} = 10V,V _{DS} = 30V,I _D = 3.0A		13.8		nC
Gate-Source Charge	Q _{gs}			2.2		
Gate-Drain Charge	Q _{gd}			1.9		
Reverse Recovery Chrage	Q _{rr}	I _F = 3A, di/dt=100A/us		7.6		ns
Reverse Recovery Time	t _{rr}			30		
Turn-on Delay Time	t _{D(on)}	V _{GS} = 10V, V _{DS} = 30V, I _D = 1.5A R _{GEN} = 3Ω		3		
Turn-on Rise Time	t _r			18		
Turn-off Delay Time	t _{D(off)}			17		
Turn-off fall Time	t _f			22		

A. Pulse Test: Pulse Width≤300us, Duty cycle ≤2%.

B. R_{θJA} is the sum of the junction-to-lead and lead-to-ambient thermal resistance, where the lead thermal reference is defined as the solder mounting surface of the drain pins. R_{θJL} is guaranteed by design, while R_{θJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



■ Typical Performance Characteristics

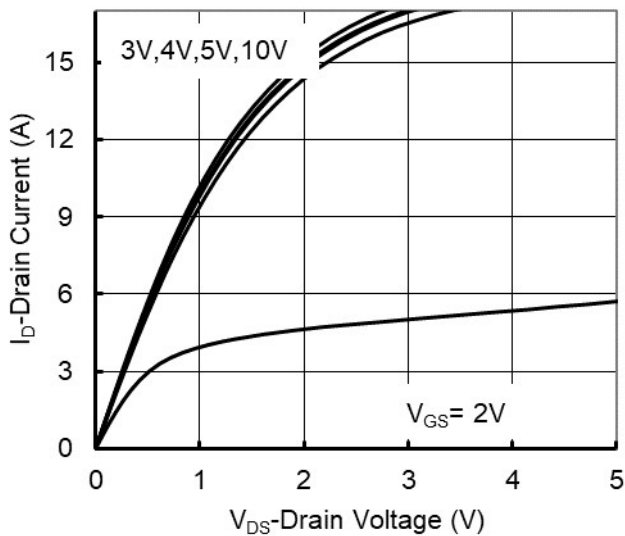


Figure1. Output Characteristics

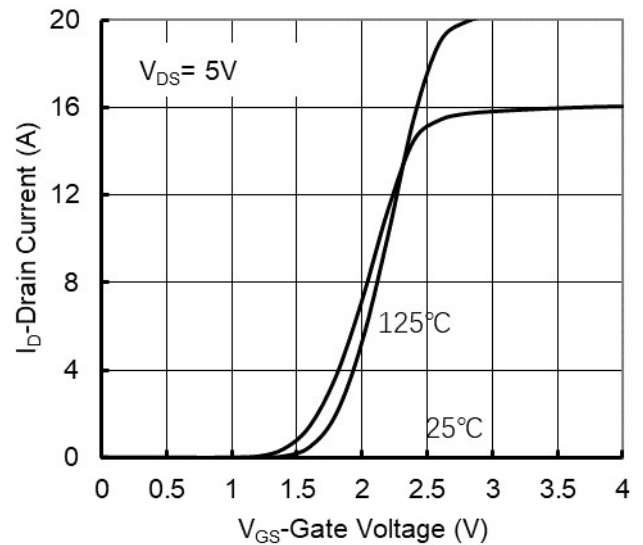


Figure2. Transfer Characteristics

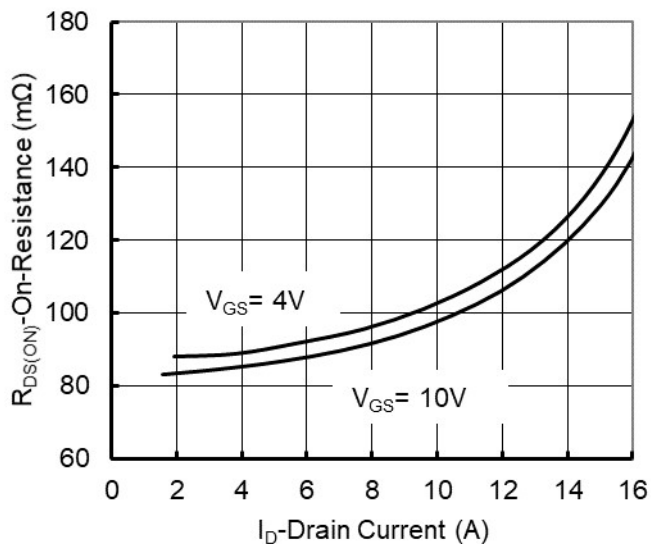


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

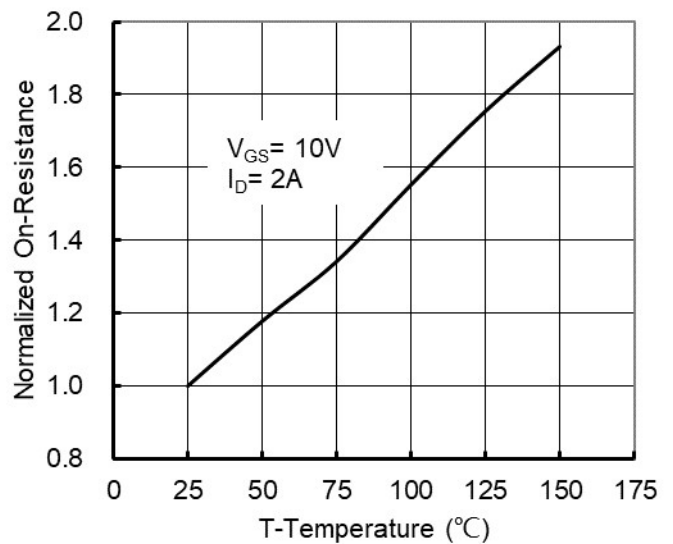


Figure 4: On-Resistance vs. Junction Temperature

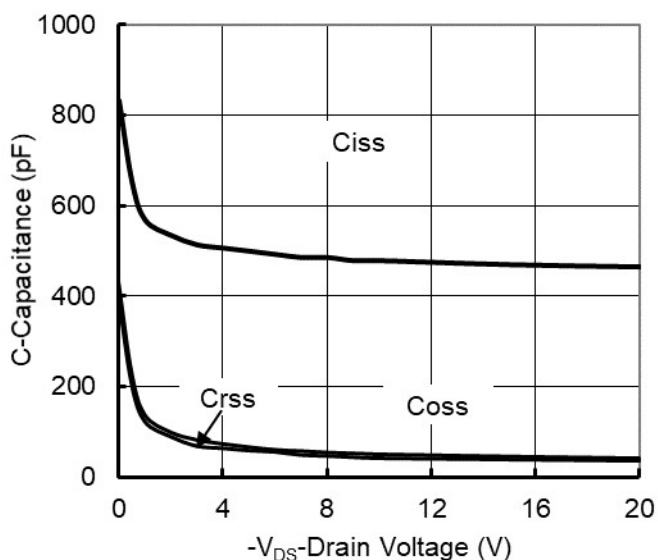


Figure5. Capacitance Characteristics

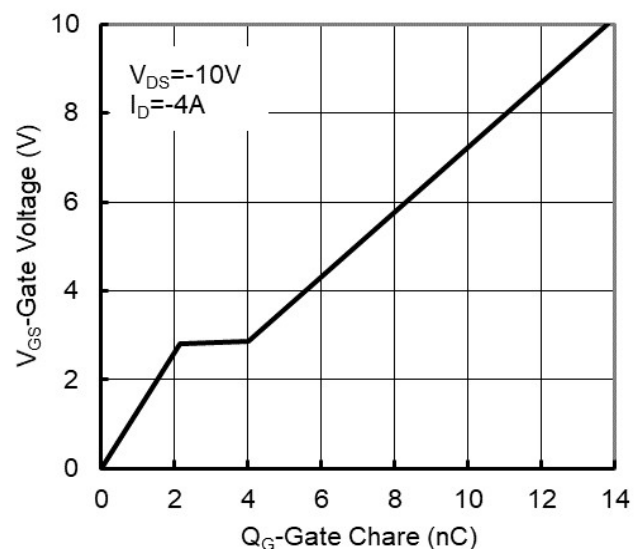


Figure6. Gate Charge

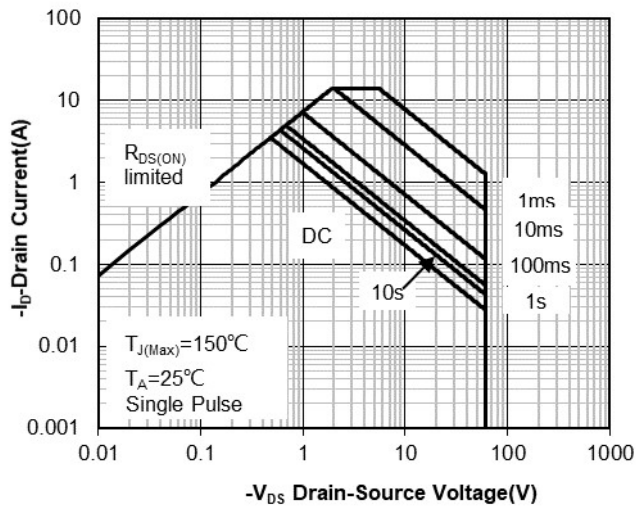


Figure7. Safe Operation Area

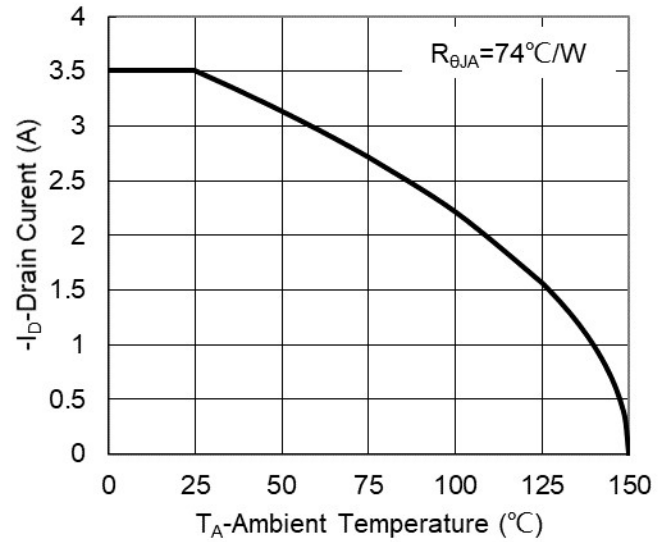


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

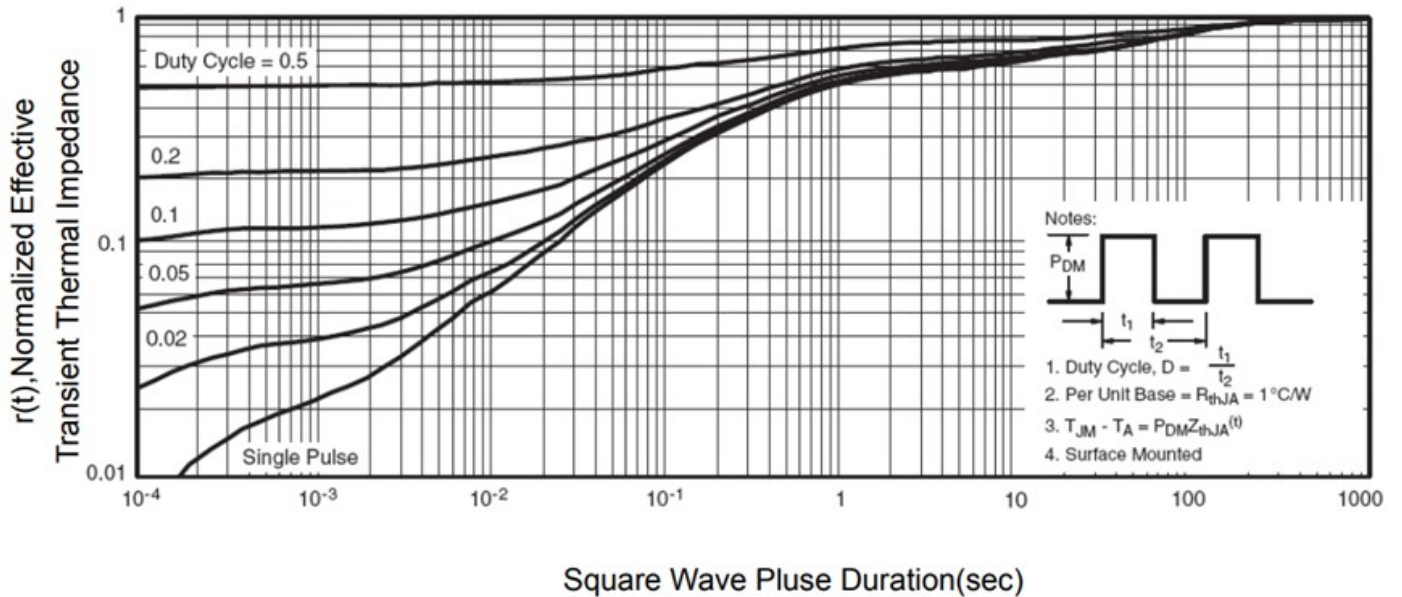
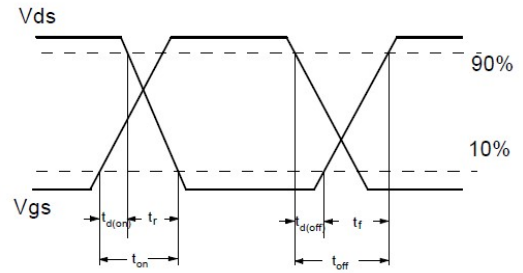
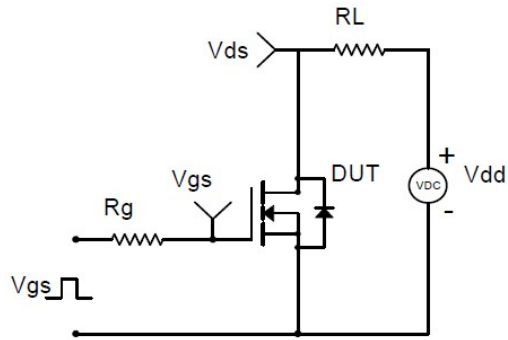
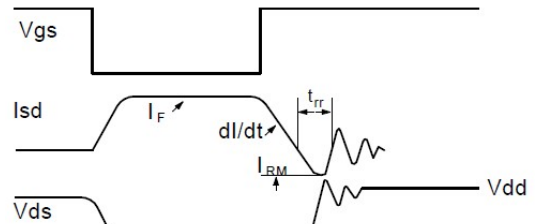
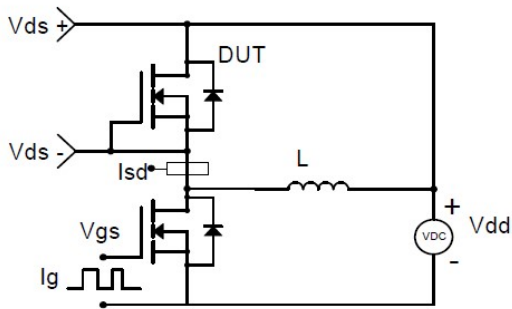


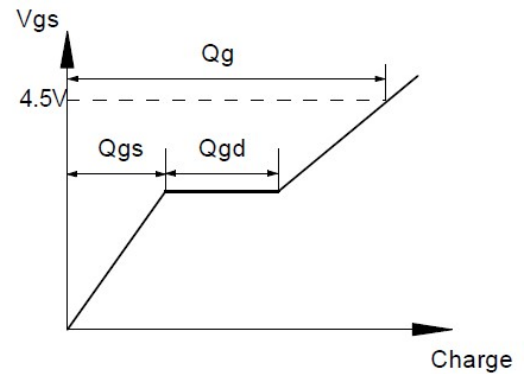
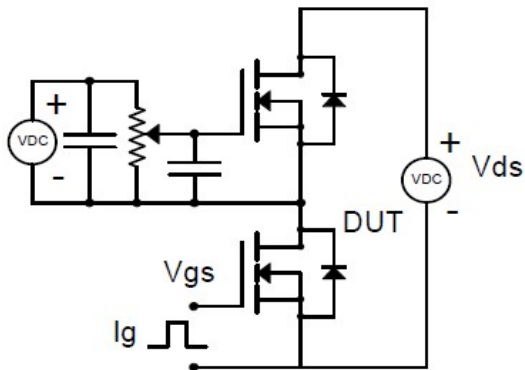
Figure9. Normalized Maximum Transient Thermal Impedance



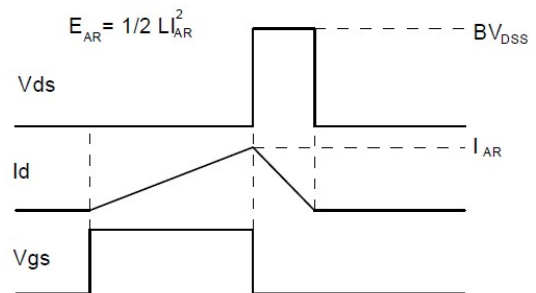
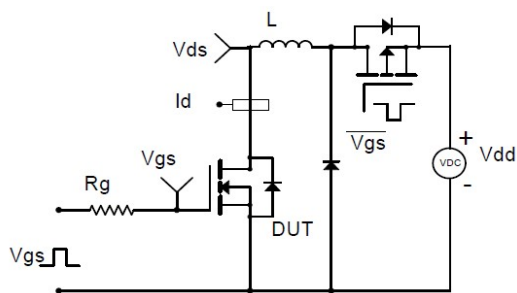
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



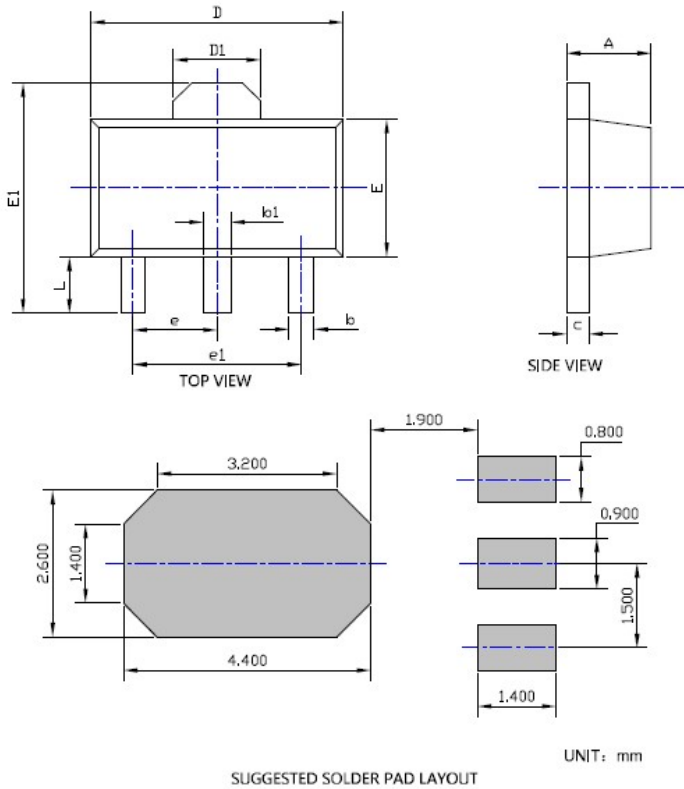
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



■ SOT-89 Package Information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.055	0.059	0.063	1.400	1.500	1.600
b	0.014	---	0.020	0.350	---	0.520
b1	0.016	---	0.023	0.400	---	0.580
c	0.014	---	0.017	0.350	---	0.440
D	0.173	0.177	0.181	4.400	4.500	4.600
D1	0.061REF			1.550REF		
E	0.093	0.096	0.100	2.350	2.450	2.550
E1	0.155	---	0.167	3.940	---	4.250
e	0.059TYP			1.500TYP		
e1	0.118TYP			3.000TYP		
L	0.035	0.039	0.043	0.900	1.000	1.100

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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